

SOD-323 Plastic-Encapsulate Diodes

SD103AWS-SD103CWS SCHOTTKY DIODES

FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- Negligible Reverse Recovery Time
- Low Reverse Capacitance



Maximum Ratings and Electrical Characteristics, Single Diode @T_A=25°C

Parameter	Symbol	SD103AWS	SD103BWS	SD103CWS	Unit
Peak Repetitive Peak reverse voltage	V _{RRM}				
Working Peak	V _{RWM}	40	30	20	V
DC Blocking Voltage	V _R				
RMS Reverse Voltage	V _{R(RMS)}	28	21	14	V
Forward Continuous Current	I _{FM}	350			mA
Repetitive Peak Forward Current @t≤1.0s	I _{FRM}	1.5			A
Power Dissipation	P _d	200			mW
Thermal Resistance Junction to Ambient	R _{θJA}	300			°C/W
Storage temperature	T _{STG}	-65~+125			°C

Electrical Ratings @T_A=25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	V _{(BR)R}				V	
SD103AWS		40				I _R =100μA
SD103BWS		30				I _R =100μA
SD103CWS		20				I _R =100μA
Forward voltage	V _F			0.37 0.60	V	I _F =20mA I _F =200mA
Reverse current	I _{RM}			5.0	μA	V _R =30V
SD103AWS						V _R =20V
SD103BWS						V _R =10V
SD103CWS						
Capacitance between terminals	C _T			50	pF	V _R =0V, f=1.0MHz
Reverse Recovery Time	t _{rr}		10		ns	I _F =I _R =200mA I _{rr} =0.1X I _R , R _L =100Ω



Typical Characteristics

SD103AWS-SD103CWS

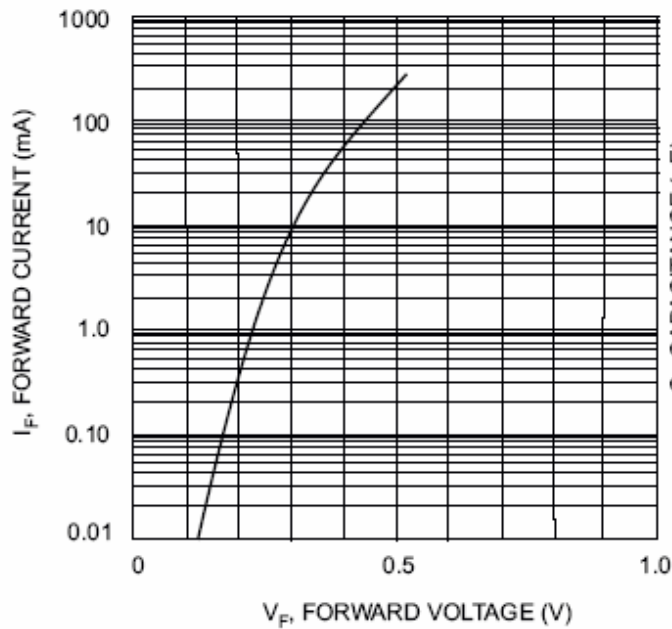


Fig. 1 Typical Forward Characteristics

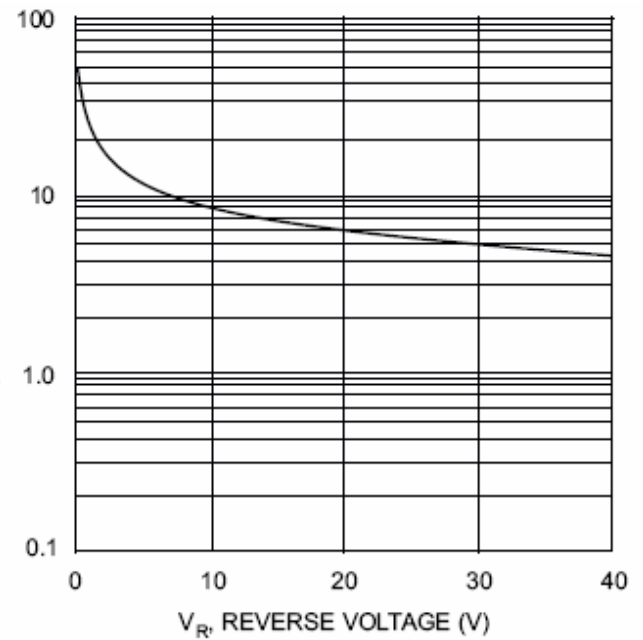


Fig. 2 Typ. Junction Capacitance vs Reverse Voltage